

1     ABSTRACT OF THE DISCLOSURE

2             The invention encompasses a method of forming a silicon-doped  
3     aluminum oxide. Aluminum oxide and silicon monoxide are co-  
4     evaporated. Subsequently, at least some of the evaporated aluminum  
5     oxide and silicon monoxide is deposited on a substrate to form the  
6     silicon-doped aluminum oxide on the substrate. The invention also  
7     encompasses methods of forming transistors and flash memory devices.  
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